



NPN TRIPLE DIFFUSED PLANAR SILICON TRANSISTOR

- High Collector-Base Voltage($V_{CBO}=1500V$)
- High Speed Switching

[illegible]

ELECTRICAL CHARACTERISTICS (T_A=25°C)

Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
Collector- Emitter Cutoff Current($V_{BE}=0$)	ICES	$V_{CE}=600\text{ V}$, $R_{BE}=0$			1.0	mA
Collector Cutoff Current	ICBO	$V_{CB}= 800\text{ V}$, $I_E=0$			10	μA
Emitter Cutoff Current	IEBO	$V_{EB}= 4\text{ V}$, $I_C=0$			1.0	mA
DC Current Gain	hFE	$V_{CE}= 5\text{ V}$,	8			
Collector- Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=1\text{A}$ $I_C=4\text{A}$, $I_B=0.8\text{A}$			5.0	V